

Supporting Information

The Transition of Type-I to Type-II SiC/GaN Heterostructure by external strain

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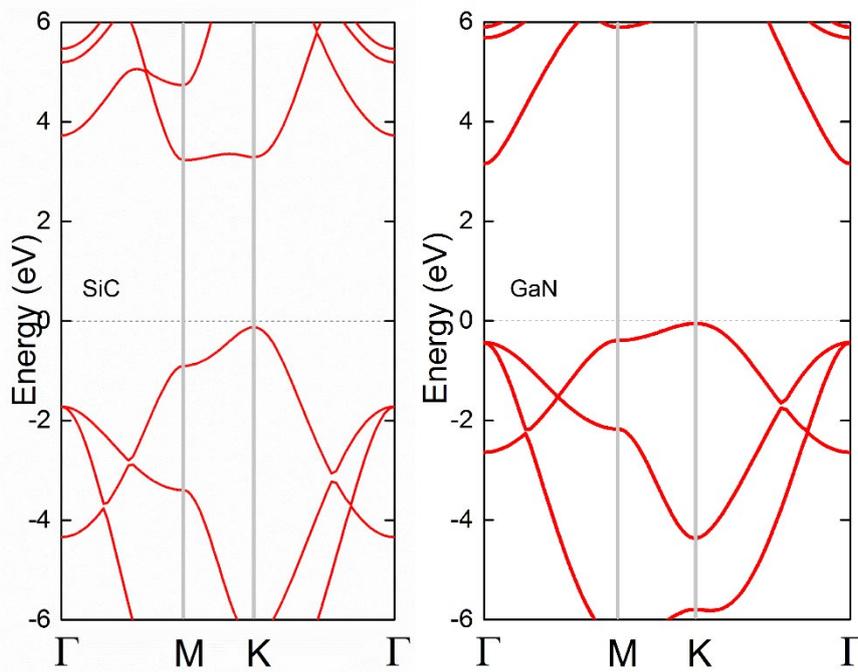


Figure S1. The band structure of the SiC and GaN monolayers calculated by HSE06 function.

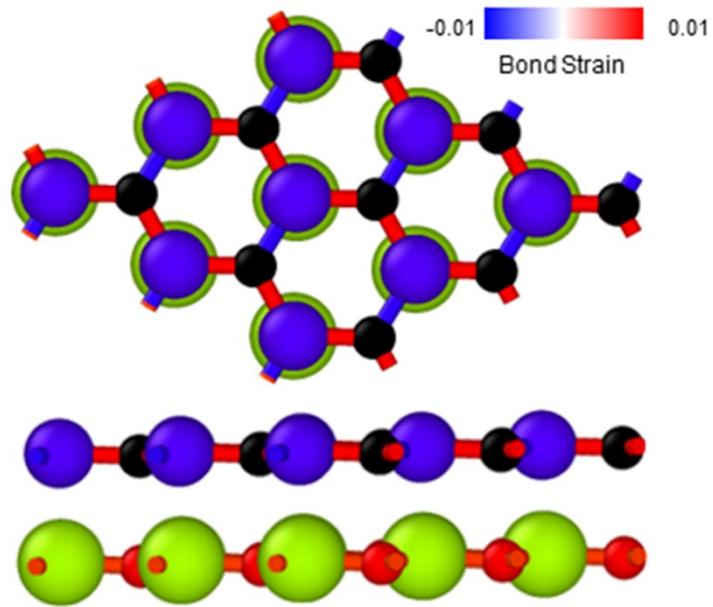


Figure S2. The bond strain of the SiC and GaN monolayers.